

# *Enabling Connected Intelligence*

22FDX for Cost-Effective Low Energy Designs

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GLOBALFOUNDRIES®

# Realizing Cost-Effective Low Energy Designs

1 22FDX<sup>®</sup> Technology & Enablement

2 22FDX<sup>®</sup> with Back Gate Bias

3 22FDX<sup>®</sup> Technology Benefits

4 22FDX<sup>®</sup> Ecosystem Expansion

# GF CMOS Roadmap Redefines Mainstream

## Applications:

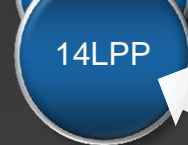
- Servers
- HPC
- Graphics
- High-end AP
- Core networking
- Auto high-end ADAS

## Premium Tier

## Features:

- High-performance
- Balanced-cost

## High Performance Computing FinFET



## Wireless, Battery-Powered Computing FD-SOI



## Applications:

- Low & mid AP
- IoT
- Autonomous vehicles
- Mobile camera

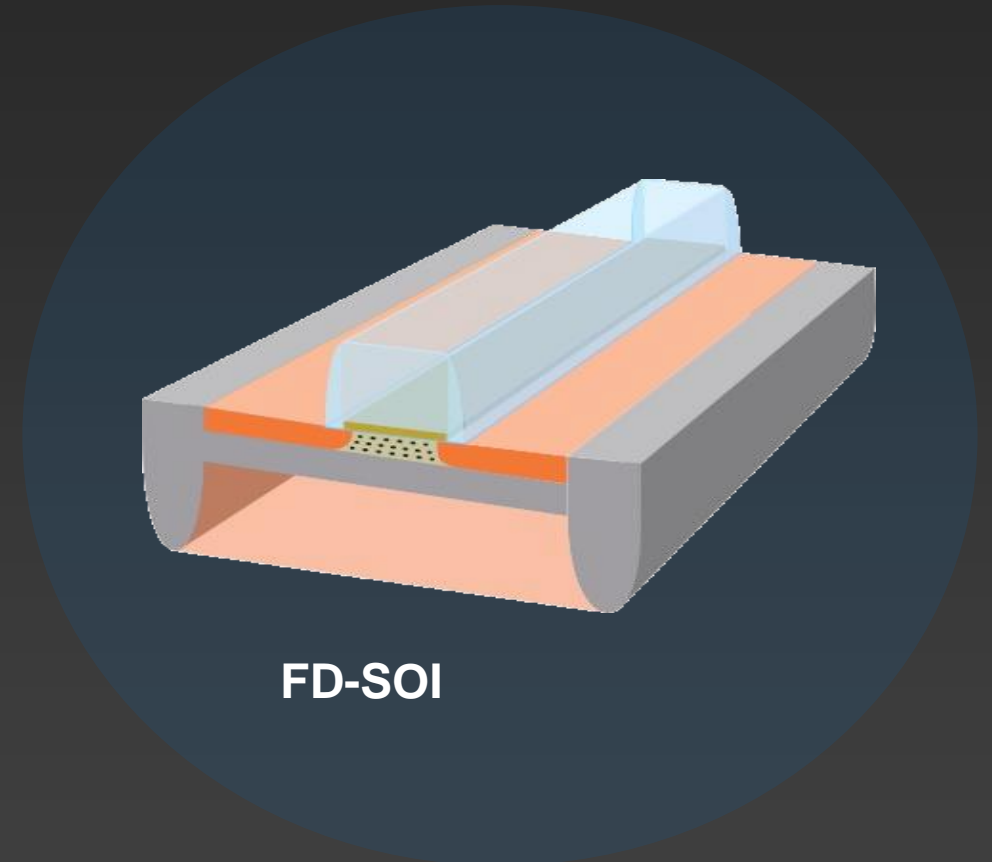
## Volume Tier

## Features:

- Low-power
- Cost-effective performance
- High Performance RF and mmWave
- Embedded memory

# 22FDX<sup>®</sup> Platform from GLOBALFOUNDRIES

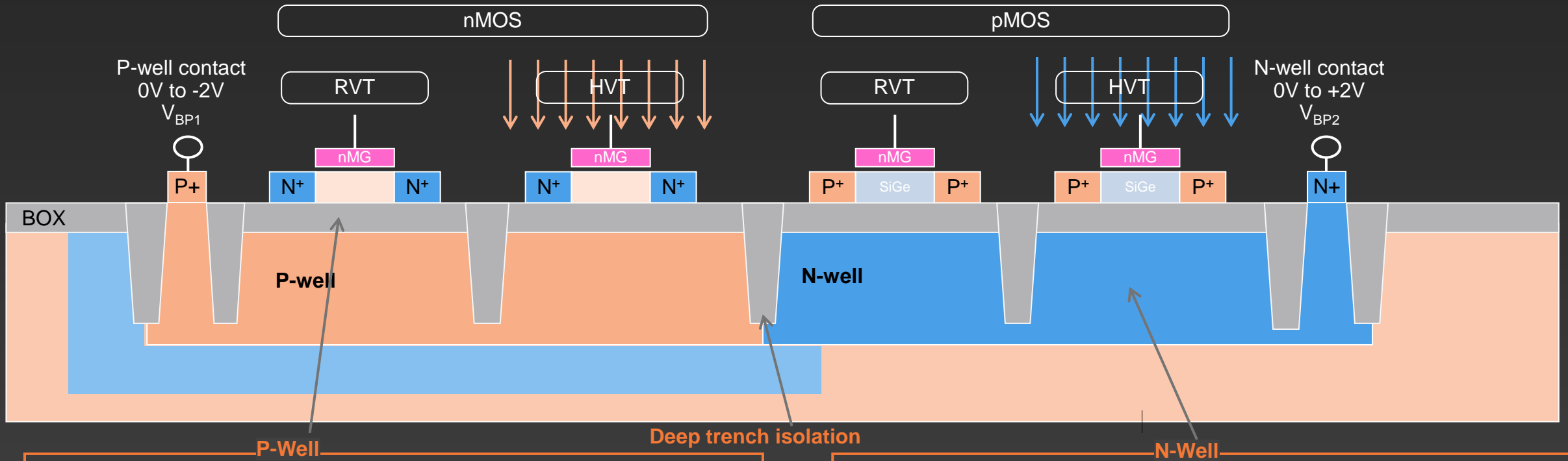
- Architected for:
  - FinFET performance at 28nm die cost
  - Emerging products in IoT, Mobile, and RF
- Enables differentiated customer solutions
  - Software-controlled body-bias
  - Energy efficiency
    - Ultra-low voltage (0.4V)
    - Ultra-low leakage (1pA/μm)
  - RF integration with high  $f_T/f_{MAX}$
  - Integrated power management



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# Reverse Back Bias Blocks

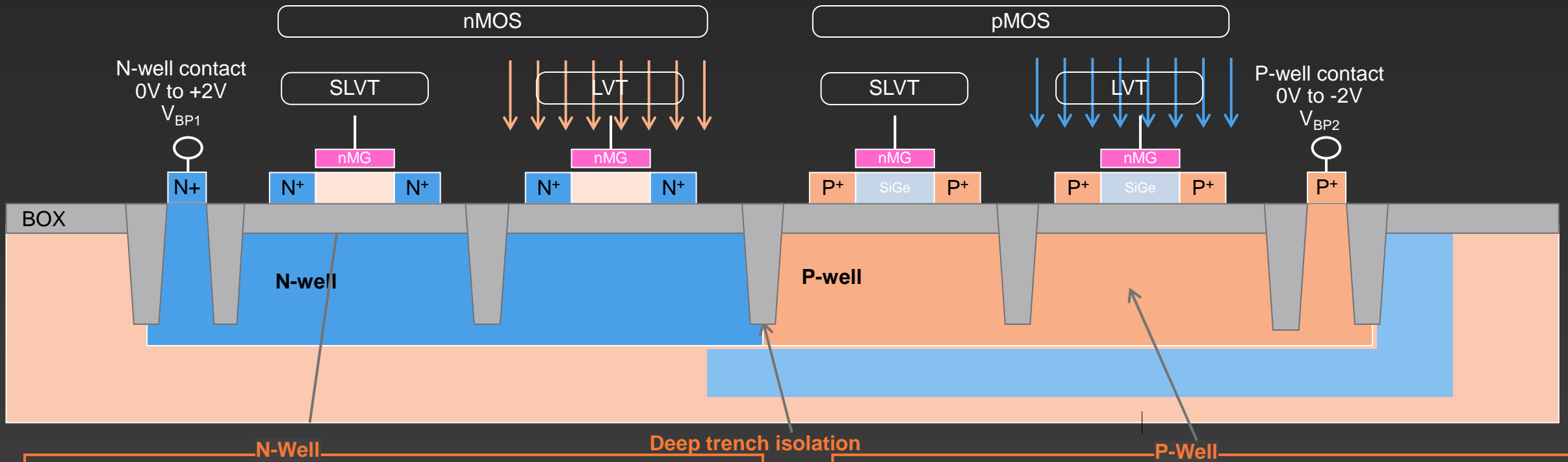


Within a P-well, the flavor of the transistors can be changed by using a lightly p-doped channel implant

Within a N-well, the flavor of the transistors can be changed by using a lightly n-doped channel implant

- ❑ RVT/HVT are **swappable post PnR** without area scaling impact
- ❑ **Full RBB capability** is possible with standard well scheme
- ❑ Gate length sizing for **additional  $V_t$ /loff control**

# Forward Body Bias Blocks



Within a N-well, the flavor of the transistors can be changed by using a lightly p-doped channel implant

Within a P-well, the flavor of the transistors can be changed by using a lightly n-doped channel implant

- ❑ SLVT/LVT are swappable post PnR without area scaling impact
- ❑ Full FBB capability is possible with flip-well scheme
- ❑ Gate length sizing for additional  $V_t$ /loff control

# Body Bias Value Proposition – ‘Trim’ & ‘Boost’

- Compensate for process, temperature, and aging variations

## Benefits:

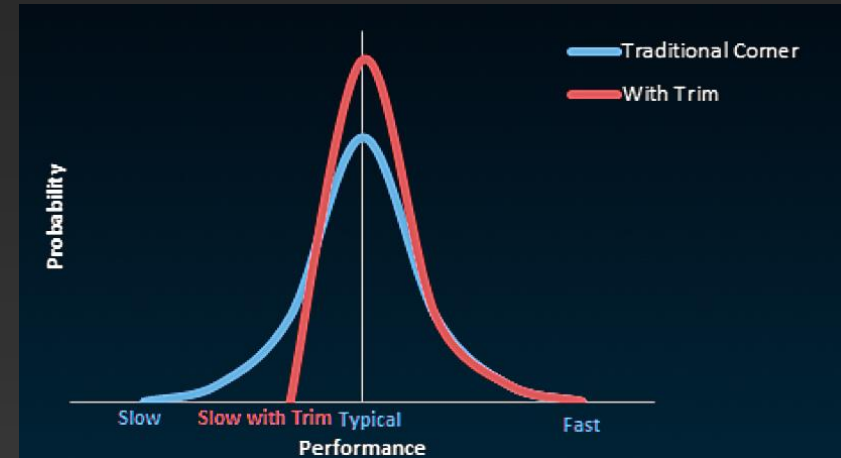
- Reduce Area
- Reduce Power
- Enables Ultra Low Voltage Operation

- Boost Performance to FinFET Speeds

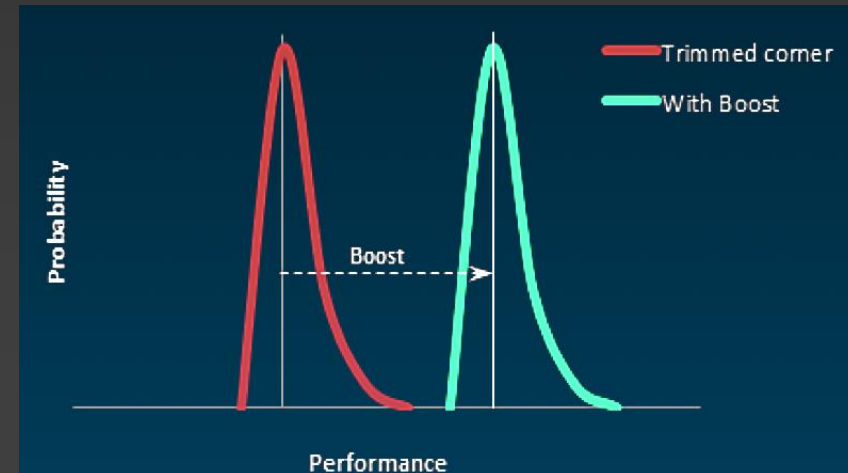
## Benefits:

- Increase Performance
- Less Dynamic Power than Voltage Scaling

## Global Corner Trimming

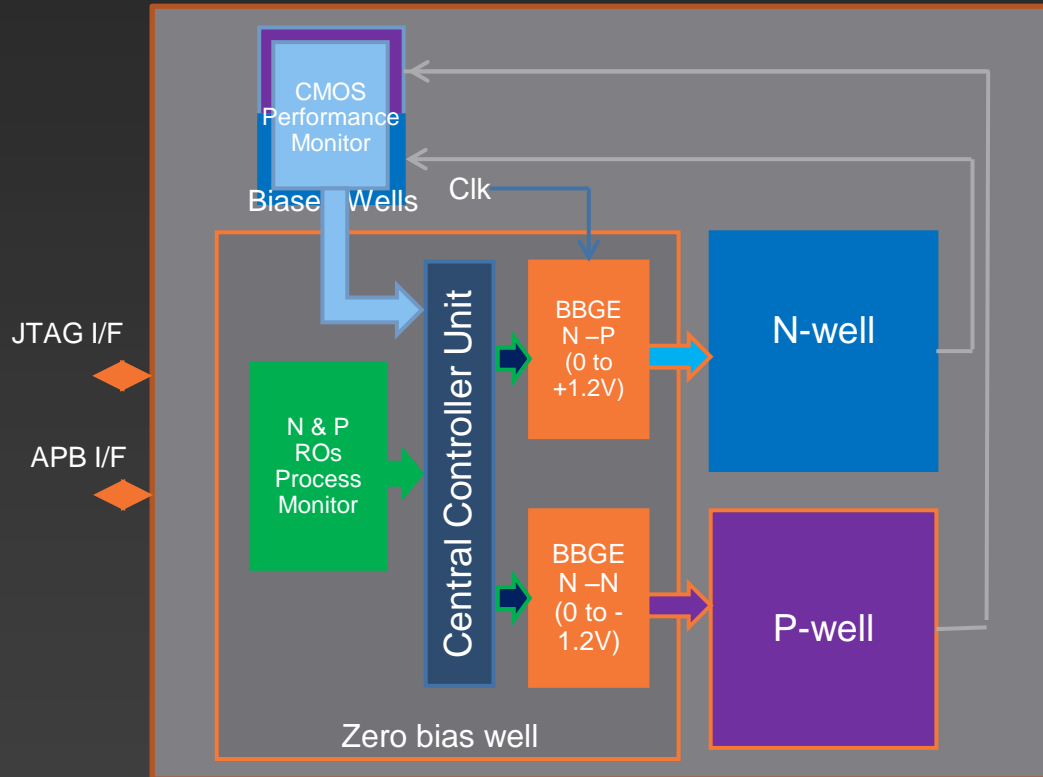


## Performance Boost





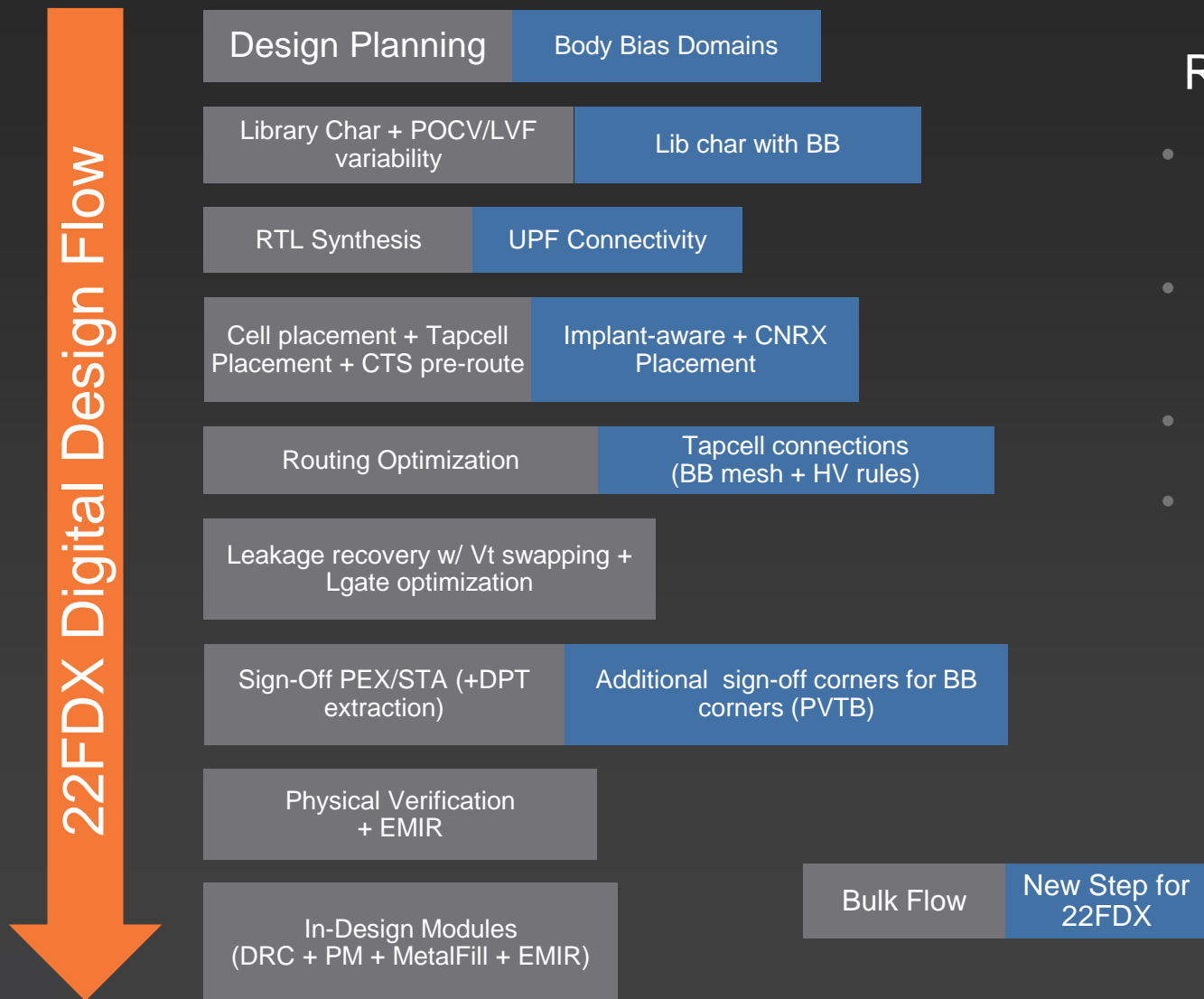
# Dynamic Global Corner Trimming Solution for IoT



- **BBGEN IP**
  - Supports 1mm<sup>2</sup> to 5mm<sup>2</sup> well area
  - Input Clock: 25MHz to 100MHz
  - Supply: 0.65Vnom - 0.8Vnom
- **Process and Performance Monitors**
  - P-fet and N-fet RO's for initial bring-up and dynamic tuning
  - CMOS Performance Monitor for dynamic tuning based on process and temperature
- **APB interface** for user control of Bias Generator
- **JTAG interface** for observability and controllability during Testing
  - **Ultra low voltage standard cell library**
  - **Ultra low voltage memories**

# 22FDX<sup>®</sup> Ultra Low Power Reference Flow

Cadence and Synopsys Certified



Reference flow adapted to ULP library

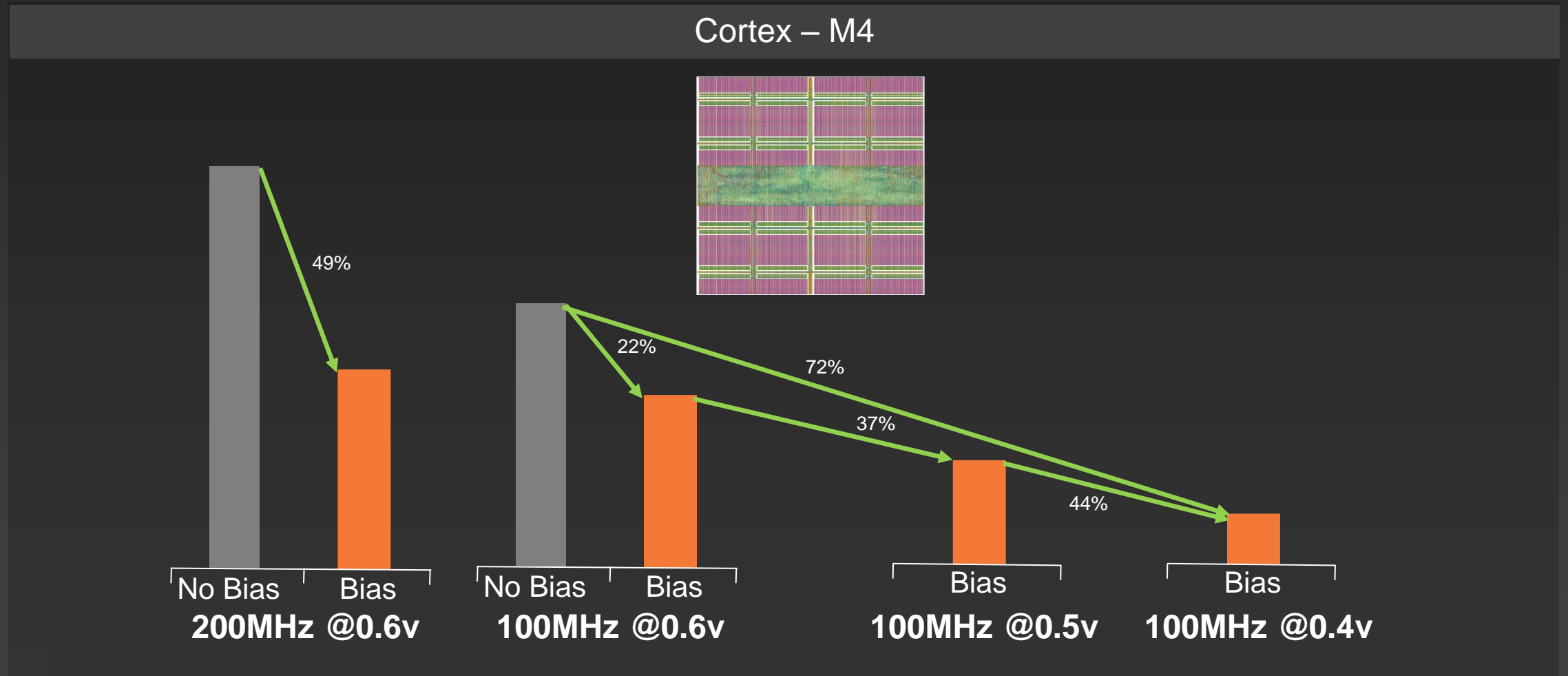
- 7.5T, 116CPP physical design setup (units, track plan, PG mesh)
- ULP corner & margin setup for implementation and sign-off
- UPF set up
- Body bias physical design elements
  - Tap cell placement
  - BB net routing

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# Arm<sup>®</sup> Cortex<sup>®</sup>-M4 – Back Gate Bias Benefit

72% Power Advantage achieved with Low Voltage and Bias Trimming



Bias-Trimming: Mixed Vt achieved > 300MHz at 0.4V, and a Customer Application is achieving > 500MHz at 0.4V.

# 22FDX - Demonstrator Description

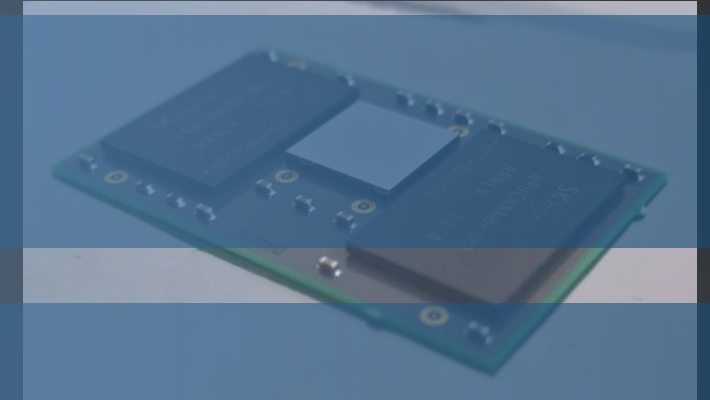
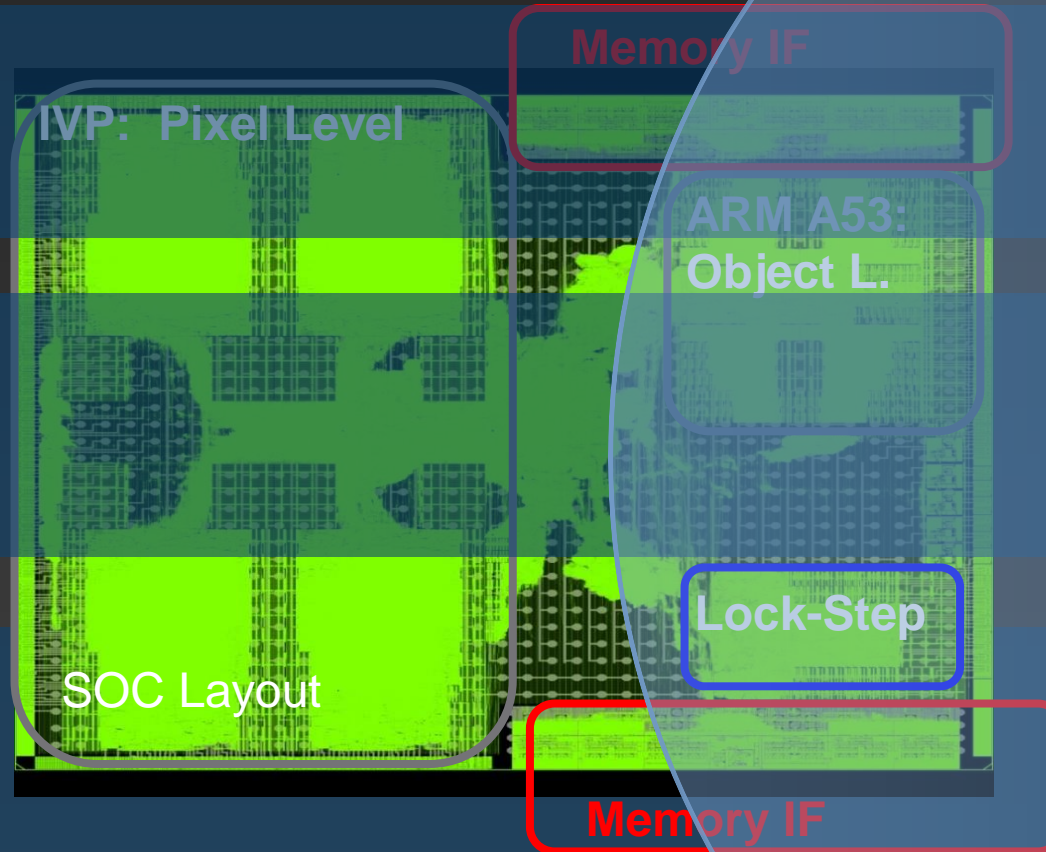
ADAS Demonstrator for image recognition / classification, image warping and Real-Time Processing

## Collaboration Partners:

DREAMCHIP, CADENCE, INVECAS, GF, Arm, ArterisIP

## Targeted Use-Cases:

- In-vehicel Image Processing
- Image recognition
- ADAS Development Platform
- Industrial Automation



System-Module (Chip + LPDDR4)



360° Surround View Demo Setup  
Demo-Car with 4 cameras

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# FDX™ Ecosystem



- Global Program **FDXcelerator™**
- Special Programs : Germany, Europe

IP, EDA, Design Services,  
ASICs, Reference  
Platforms, Packaging and  
Test Solutions

Design &  
Development

Customers and FDX™  
Ecosystem

Manufacturing

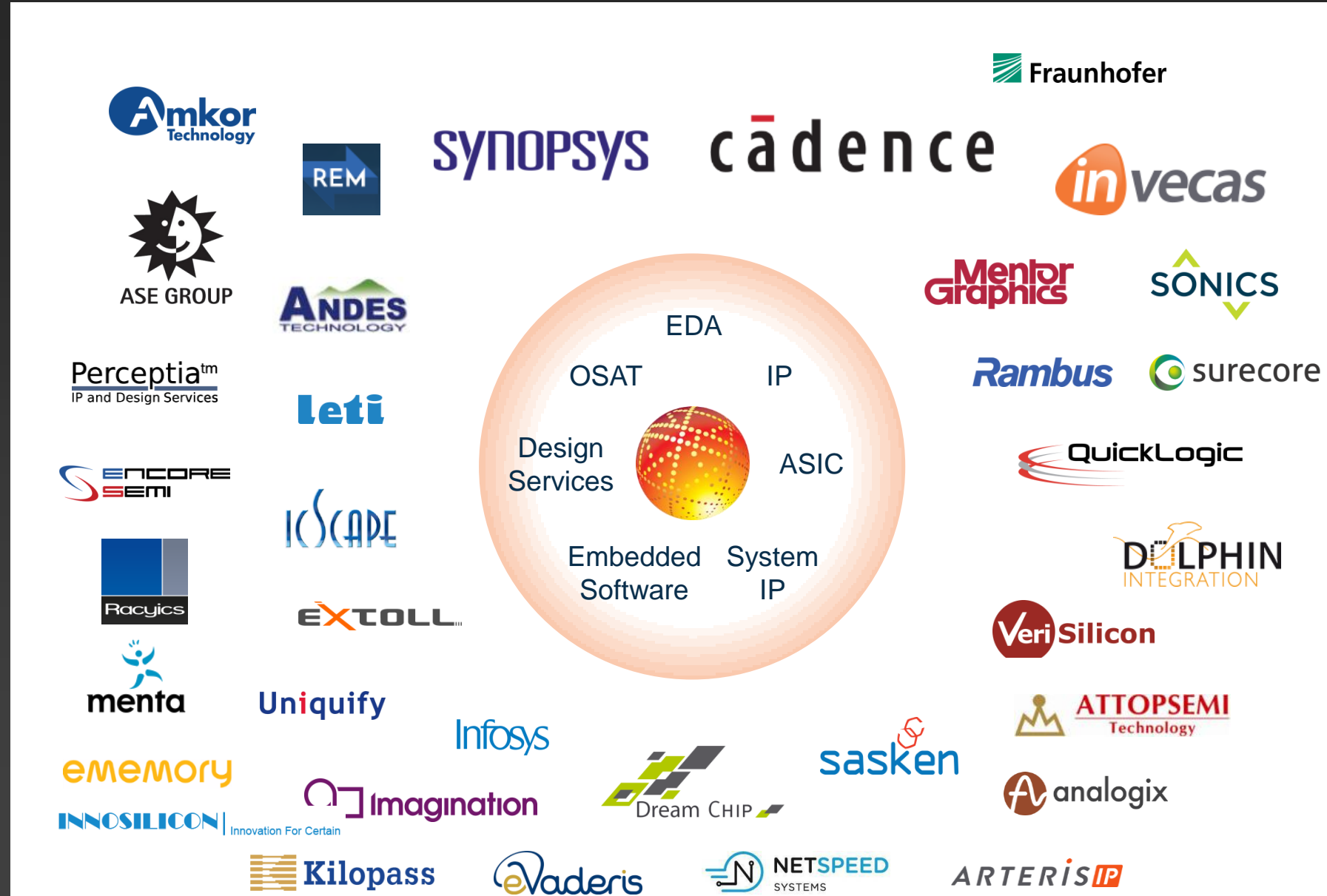
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# FDXcelerator™ Ecosystem Partnering for Growth

Reduce time to market and facilitate FDX™ SoC product design

- Easy access to plug and play solutions
- Minimizes customer development costs
- Lowers barriers of migration

~ 40





# Building Global Scale for FDX™

## Govt, GF, Partners & Customers invest to expand FD-SOI ecosystem

- Commitment to regional growth
  - IP Development
  - Design Services
  - Fabless Companies
  - Training & Curriculum

## Local Customer Benefits

- Local manufacturing
- Accelerate SoC TTM
  - Local capability & support
- Growth of engineering talent
- Expand Local semiconductor Innovation and expertise with strong government support

Dresden, Germany



45nm – 22nm

Chengdu, China



180nm – 12nm

## Chengdu, China Fab 11

- New 300mm fab
- 180nm/130nm production starting 2H18
- FDX in 2H19

## Dresden, Germany Fab 1

- Expanding 22FDX® FD-SOI capacity by 40% by 2020
- Developing derivatives (RF, Auto, eMRAM)

# GLOBALFOUNDRIES and Academic Collaboration

## Value creation through collaborative University programs

- Access to circuit design
- Access to global shuttles
- Customer and business opportunity focus
- Strong drive for innovation



## Summary

- 22FDX<sup>®</sup> Platform is fully enabled with a Comprehensive IP Portfolio
- Back Gate Bias Trimming Solutions Methodology available for benchmark Performance/Watt and Ultra-Low Power
- 22FDX: Proven SOC capability with ADAS Demonstrator
- 22FDX Ecosystem is thriving
  - Partners are delivering broad and unique solutions for 22FDX
  - Providing wide development / solution footprint



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Thank you

***Enabling Connected Intelligence***

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